## Features

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected
- Totally Lead-Free \& Fully RoHS Compliant (Notes 1 \& 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DMG1013UWQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.
https://www.diodes.com/quality/product-definitions/


## Mechanical Data

- Case: SOT323
- Case Material: Molded Plastic, "Green" Molding Compound.

UL Flammability Classification Rating 94V-0

- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminals: Finish - Matte Tin Annealed over Alloy 42 Leadframe.

Solderable per MIL-STD-202, Method 208 (3)

- Weight: 0.006 grams (Approximate)


Top View


Eauivalent Circuit


Ton View

## Ordering Information (Note 4)

| Part Number | Case | Packaging |
| :---: | :---: | :---: |
| DMG1013UWQ-7 | SOT323 | $3000 /$ Tape \& Reel |
| DMG1013UWQ-13 | SOT323 | $10000 /$ Tape \& Reel |

Notes: $\quad$ 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) \& 2015/863/EU (RoHS 3) compliant.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain $<900 \mathrm{ppm}$ bromine, $<900 \mathrm{ppm}$ chlorine ( $<1500 \mathrm{ppm}$ total $\mathrm{Br}+\mathrm{Cl}$ ) and <1000ppm antimony compounds.
4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

## Marking Information



PA1 = Product Type Marking Code
YM or $\bar{Y} M=$ Date Code Marking
Y or $Y=$ Year (ex: $I=2021$ )
M = Month (ex: 9 = September)

| Year | 2008 | $\ldots . .$. | 2021 | 2022 | 2023 | 2024 | 2025 | 2026 | 2027 | 2028 | 2029 | 2030 |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Code | V | $\ldots$ | I | J | K | L | M | N | 0 | P | R | S |
| Month | Jan | Feb | Mar | Apr | May | Jun | Jul | Aug | Sep | Oct | Nov | Dec |
| Code | 1 | 2 | 3 | 4 | 5 | 6 | 7 | 8 | 9 | 0 | N | D |

DMG1013UWQ

Maximum Ratings ( $@ T_{A}=+25^{\circ} \mathrm{C}$, unless otherwise specified.)

| Characteristic | Symbol | Value | Unit |  |
| :--- | :---: | :---: | :---: | :---: |
| Drain-Source Voltage | $V_{\text {DSS }}$ | -20 | V |  |
| Gate-Source Voltage | $\mathrm{V}_{\text {GSS }}$ | $\pm 6$ | V |  |
| Continuous Drain Current (Note 5) | Steady <br> State | $\mathrm{T}_{\mathrm{A}}=+25^{\circ} \mathrm{C}$ <br> $\mathrm{T}_{\mathrm{A}}=+85^{\circ} \mathrm{C}$ | $\mathrm{I}_{\mathrm{D}}$ | -0.82 |
| Pulsed Drain Current (Note 6) | $\mathrm{I}_{\mathrm{DM}}$ | A |  |  |

## Thermal Characteristics

| Characteristic | Symbol | Value | Unit |
| :--- | :---: | :---: | :---: |
| Power Dissipation (Note 5) | $\mathrm{P}_{\mathrm{D}}$ | 0.31 | W |
| Thermal Resistance, Junction to Ambient | @ $\mathrm{T}_{\mathrm{A}}=+25^{\circ} \mathrm{C}($ Note 5) | $\mathrm{R}_{\theta \mathrm{JA}}$ | 398 |
| Operating and Storage Temperature Range | $\mathrm{T}_{\mathrm{J},} \mathrm{T}_{\mathrm{STG}}$ | -55 to +150 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |

Notes: $\quad$ 5. Device mounted on FR-4 PCB, with minimum recommended pad layout.
6. Repetitive rating, pulse width limited by junction temperature.

Electrical Characteristics (@ $\mathrm{T}_{\mathrm{A}}=+25^{\circ} \mathrm{C}$, unless otherwise specified.)

| Characteristic | Symbol | Min | Typ | Max | Unit | Test Condition |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| OFF CHARACTERISTICS (Note 7) |  |  |  |  |  |  |
| Drain-Source Breakdown Voltage | BV ${ }_{\text {DSS }}$ | -20 | - | - | V | $\mathrm{V}_{\mathrm{GS}}=0 \mathrm{~V}, \mathrm{I}_{\mathrm{D}}=-250 \mu \mathrm{~A}$ |
| Zero Gate Voltage Drain Current $\mathrm{T}_{J}=+25^{\circ} \mathrm{C}$ | IDSs | - | - | -100 | nA | $V_{D S}=-20 \mathrm{~V}, \mathrm{~V}_{\mathrm{GS}}=0 \mathrm{~V}$ |
| Gate-Source Leakage | Igss | - | - | $\pm 2.0$ | $\mu \mathrm{A}$ | $V_{G S}= \pm 4.5 \mathrm{~V}, \mathrm{~V}_{\mathrm{DS}}=0 \mathrm{~V}$ |
| ON CHARACTERISTICS (Note 7) |  |  |  |  |  |  |
| Gate Threshold Voltage | VGS(TH) | -0.5 | - | -1.0 | V | $\mathrm{V}_{\text {DS }}=\mathrm{V}_{\mathrm{GS}}, \mathrm{I}_{\mathrm{D}}=-250 \mu \mathrm{~A}$ |
| Static Drain-Source On-Resistance | RDS(ON) | - | $\begin{aligned} & 0.5 \\ & 0.7 \\ & 1.0 \end{aligned}$ | $\begin{gathered} 0.75 \\ 1.05 \\ 1.5 \end{gathered}$ | $\Omega$ | $\mathrm{V}_{G S}=-4.5 \mathrm{~V}, \mathrm{I}_{\mathrm{D}}=-430 \mathrm{~mA}$ |
|  |  |  |  |  |  | $\mathrm{V}_{G S}=-2.5 \mathrm{~V}, \mathrm{I}_{\mathrm{D}}=-300 \mathrm{~mA}$ |
|  |  |  |  |  |  | $\mathrm{V}_{G S}=-1.8 \mathrm{~V}, \mathrm{I}_{\mathrm{D}}=-150 \mathrm{~mA}$ |
| Forward Transfer Admittance | $\left\|\mathrm{Y}_{\mathrm{fs}}\right\|$ | - | 0.9 | - | S | $V_{D S}=-10 \mathrm{~V}, \mathrm{I}_{\mathrm{D}}=-250 \mathrm{~mA}$ |
| Diode Forward Voltage | $V_{\text {SD }}$ |  | -0.8 | -1.2 | V | $\mathrm{V}_{\mathrm{GS}}=0 \mathrm{~V}, \mathrm{I}_{\mathrm{S}}=-150 \mathrm{~mA}$ |
| DYNAMIC CHARACTERISTICS (Note 8) |  |  |  |  |  |  |
| Input Capacitance | $\mathrm{C}_{\text {iss }}$ | - | 59.76 | - | pF | $\begin{aligned} & V_{D S}=-16 \mathrm{~V}, V_{G S}=0 V, \\ & f=1.0 \mathrm{MHz} \end{aligned}$ |
| Output Capacitance | Coss | - | 12.07 | - | pF |  |
| Reverse Transfer Capacitance | $\mathrm{C}_{\text {rss }}$ | - | 6.36 | - | pF |  |
| Total Gate Charge | $\mathrm{Q}_{\mathrm{g}}$ | - | 622.4 | - | pC | $\begin{aligned} & V_{G S}=-4.5 \mathrm{~V}, V_{D S}=-10 \mathrm{~V}, \\ & I_{D}=-250 \mathrm{~mA} \end{aligned}$ |
| Gate-Source Charge | $\mathrm{Qg}_{\mathrm{gs}}$ | - | 100.3 | - | pC |  |
| Gate-Drain Charge | $\mathrm{Q}_{\mathrm{gd}}$ | - | 132.2 | - | pC |  |
| Turn-On Delay Time | $\mathrm{t}_{\text {(ON })}$ | - | 5.1 | - | ns | $\begin{aligned} & V_{D D}=-10 \mathrm{~V}, V_{G S}=-4.5 \mathrm{~V}, \\ & R_{L}=47 \Omega, R_{G}=10 \Omega, \\ & I_{D}=-200 \mathrm{~mA} \end{aligned}$ |
| Turn-On Rise Time | $t_{R}$ | - | 8.1 | - | ns |  |
| Turn-Off Delay Time | $t_{\text {d(OFF) }}$ | - | 28.4 | - | ns |  |
| Turn-Off Fall Time | $\mathrm{t}_{\mathrm{F}}$ | - | 20.7 | - | ns |  |

Notes: 7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to production testing.


Figure 1. Typical Output Characteristic


Figure 3. Typical On-Resistance vs Drain Current and Gate Voltage


Figure 5. Typical On-Resistance vs Drain Current and Junction Temperature


$\mathrm{V}_{\mathrm{GS}}$, GATE-SOURCE VOLTAGE (V)
Figure 4. Typical Transfer Characteristic

$\mathrm{T}_{\mathrm{J}}$, JUNCTION TEMPERATURE $\left({ }^{\circ} \mathrm{C}\right)$
Figure 6. On-Resistance Variation with Junction Temperature

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Figure 7. On-Resistance Variation with Junction Temperature


Figure 9. Diode Forward Voltage vs Current



Figure 8. Gate Threshold Variation vs Junction Temperature


Figure 10. Typical Total Capacitance


Figure 12. Transient Thermal Resistance

## Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

## SOT323



| SOT323 |  |  |  |  |
| :---: | :---: | :---: | :---: | :---: |
| Dim | Min | Max | Typ |  |
| A1 | 0.00 | 0.10 | 0.05 |  |
| A2 | 0.90 | 1.00 | 0.95 |  |
| b | 0.25 | 0.40 | 0.30 |  |
| c | 0.10 | 0.18 | 0.11 |  |
| D | 1.80 | 2.20 | 2.15 |  |
| E | 2.00 | 2.20 | 2.10 |  |
| E1 | 1.15 | 1.35 | 1.30 |  |
| e | 0.650 BSC |  |  |  |
| e1 | 1.20 | 1.40 | 1.30 |  |
| F | 0.375 | 0.475 | 0.425 |  |
| L | 0.25 | 0.40 | 0.30 |  |
| a | $8^{\circ}$ |  |  |  |
| All Dimensions in $\mathbf{~ m m}$ |  |  |  |  |
|  |  |  |  |  |

## Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.
SOT323


| Dimensions | Value <br> (in mm) |
| :---: | :---: |
| $\mathbf{C}$ | 0.650 |
| $\mathbf{G}$ | 1.300 |
| $\mathbf{X}$ | 0.470 |
| $\mathbf{Y}$ | 0.600 |
| $\mathbf{Y 1}$ | 2.500 |

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